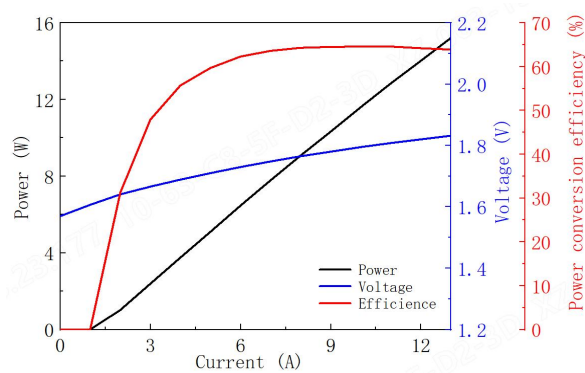


High-power Single Emitter Diode Lasers, 792nm, 10W cw
792nm 10W高功率单管激光芯片
DG-UMC-190-792-TE-10-4.0

性能参数 Performance parameters	符号 Symbol	最小值 Minimum	典型值 Typical	最大值 Maximum	单位 Unit
Operation					
输出功率 Optical output power	P_o		10		W
中心波长 Wavelength	λ_c	789	792	795	nm
冷波长@2A Wavelength@2A	λ_0	788	790	792	nm
工作模式 Operation mode			CW		
Geometrical					
发光区宽度 Emittier width	E.W.	185	190	195	μm
腔长 Cavity length	L	3995	4000	4005	μm
宽度 Width	W	495	500	505	μm
厚度 Thickness	D	100	115	130	μm
Electro Optical Data					
电光转换效率 Electro-optic conversion efficiency	η_c	58	61		%
斜率效率 Slope efficiency	SE	1.20	1.26		W/A
阈值电流 Threshold current	I_{th}		1.1	1.3	A
工作电流 Operating current	I_{op}		9	11	A
工作电压 Operating voltage	V_{op}		1.78	1.85	V
光谱宽度 Spectral width (FWHM)	$\Delta\lambda$		2	5	nm
波长温度系数 Wavelength temperature coefficient	$\Delta\lambda/\Delta T$		0.3		nm/°C
水平远场发散角 (95%E) Horizontal F.F. divergence angle	$\theta_{//}$		7	9	Deg
垂直远场发散角 (95%E) Vertical F.F. divergence angle	$\theta_{\perp}$		62	66	Deg
TE 偏振度@5A TE Polarization@5A		95.0	96.0		%

备注：本参数为产品进行COS封装，CW电流模式，导热板25°C条件下的测试参数。
Note: These parameters were obtained by testing COS packaged products in the CW mode at 25°C.

⚙ Power-Current-Voltage-Efficiency



⚙ Spectral characteristics

